4400–6500 MHz GaN MMIC Power Amplifier Die

LCI-PA-4400-6500-PS44T is a GaN MMIC power amplifier supplied as bare die for 4400–6500 MHz. It supports CW and pulsed operation.



The RF table specifies: Saturated output power: 44 dBm (typical); Power gain: 27 dB (typical); Power-added efficiency: 47 % (typical). RF test conditions: TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 17 dBm; τ = 100 µs; D = 10%. Die dimensions: 3.51 × 2.44 mm.

RF characteristics

TA = +25 °C; Vd = +28 V; Vg = -2.8 V; Pin = 17 dBm; τ = 100 µs; D = 10%

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Operating frequency	f	4400	-	6500	MHz
Saturated output power	Psat	43.5	44	-	dBm
Power gain	Gp	26.5	27	-	dB
Power-gain flatness	ΔGp	-	-	1	dB
Power-added efficiency	PAE	45	47	-	%
Small-signal gain	S21	34	35	36.5	dB
Small-signal gain flatness	ΔS21	-	-	±1.2	dB
Input VSWR	VSWR(in)	-	1.8	2	-

DC bias and current

Vd = +28 V

Parameter	Symbol	Minimum	Typical	Maximum	Value	Unit
Drain voltage	Vd	-	28	-	-	V
Gate voltage	Vg	-	-2.8	-	-	V
Quiescent drain current	Id	-	-	-	0.13	A

Absolute limits

Absolute limits; these are not normal operating targets.

Parameter	Symbol	Minimum	Typical	Maximum	Unit
Maximum drain-source voltage	Vd	-	-	32	V
Minimum gate bias	Vg	-5	-	-	V
Maximum input power	Pin	-	-	20	dBm
Maximum channel temperature	Top	-	-	200	°C
Storage temperature	TSTG	-65	-	150	°C

Die dimensions

Parameter	Value	Unit
Plan-view die dimensions	3.51 × 2.44 (Thickness is not specified.)	mm
Plan-view outline tolerance	±100 (Plan-view outline only; the source does not specify thickness tolerance.)	µm

Current publication record · 1.8 · 2026-11-12. Product description or editorial content updated. Replaces revision 1.7.

Die integration and bias sequencing

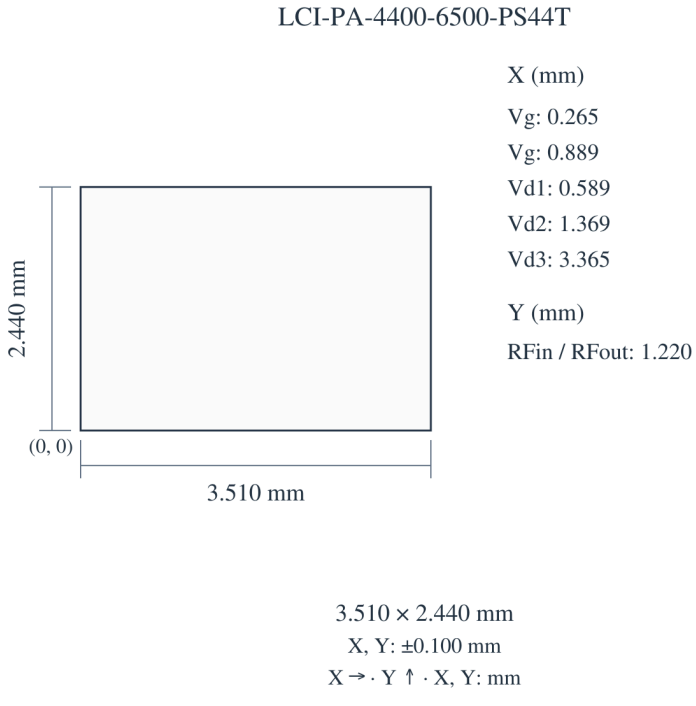
Apply gate bias before drain bias at power-up. At power-down, remove drain bias before gate bias. Use clean handling, ESD protection and a carrier with thermal expansion compatible with the SiC die.

Bond-pad dimensions

Symbol: RFin; Dimensions (µm): 100 × 100. Symbol: Vg; Dimensions (µm): 100 × 100. Symbol: Vd1; Dimensions (µm): 120 × 120. Symbol: Vd2; Dimensions (µm): 120 × 120. Symbol: Vd3; Dimensions (µm): 150 × 150. Symbol: RFout; Dimensions (µm): 110 × 120.

Mechanical Outline

Outline and dimensioned coordinates in mm. Use this drawing as a dimensional reference. Fabrication and wire bonding require complete drawings.

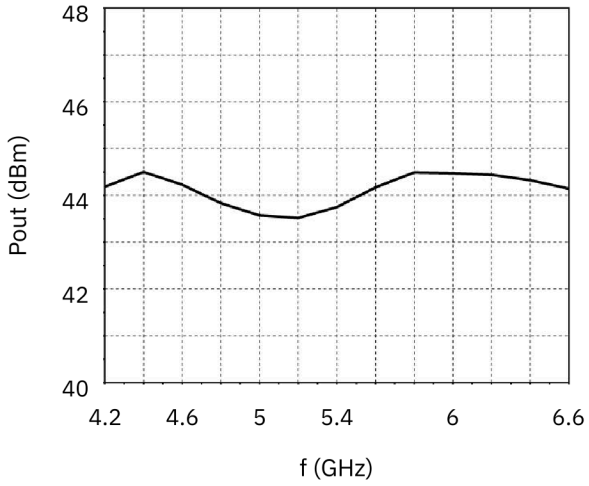


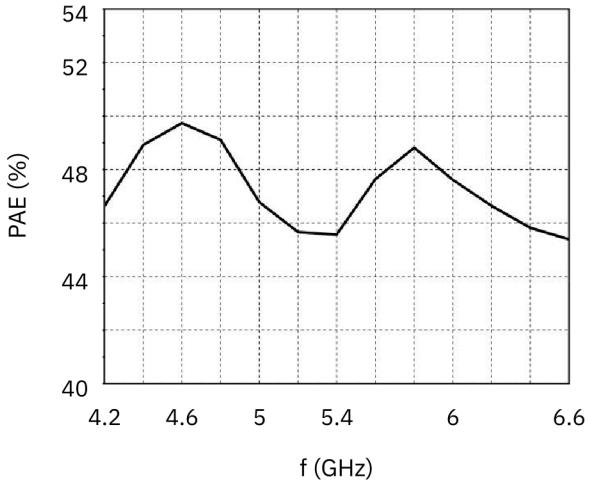
Performance curves

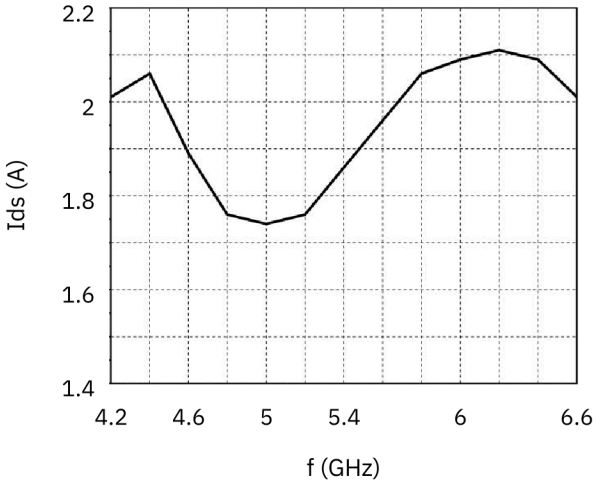
Each performance plot applies to its stated operating conditions.

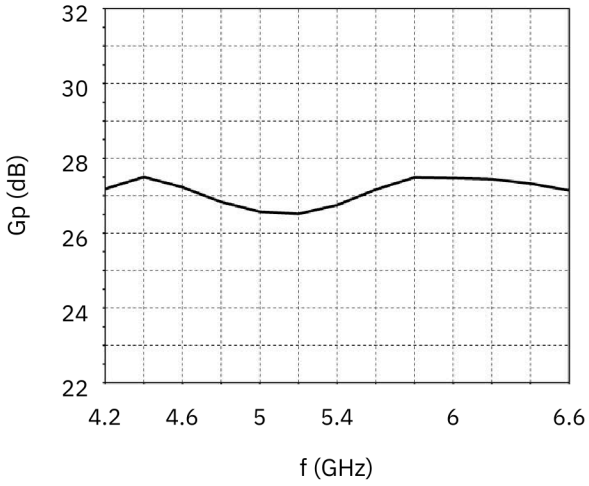
Pulsed — Saturated output power; Dynamic drain current; Power-added efficiency; Power gain.

Figure notes: TA=+25°C; Vd=+28V; Vg=-2.8V; Pin=17dBm. τ = 100 µs; D = 10%. Conditions apply to the indicated plots and their own legends.



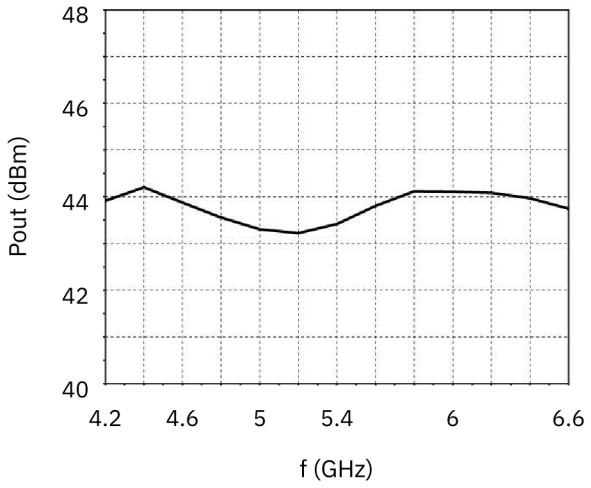


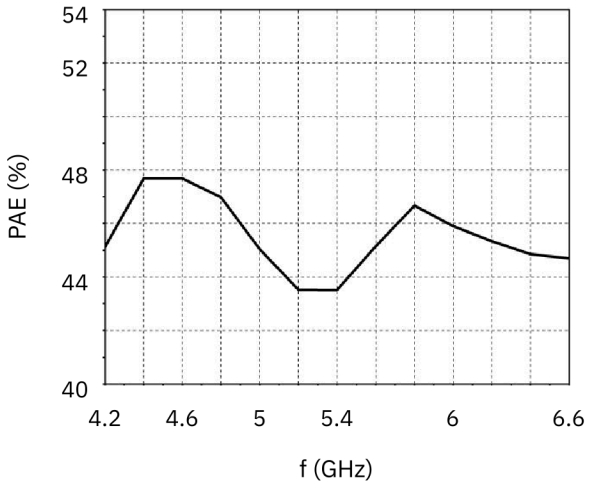


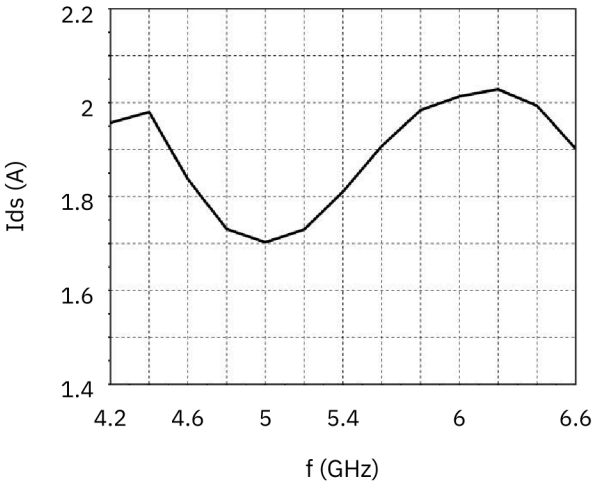


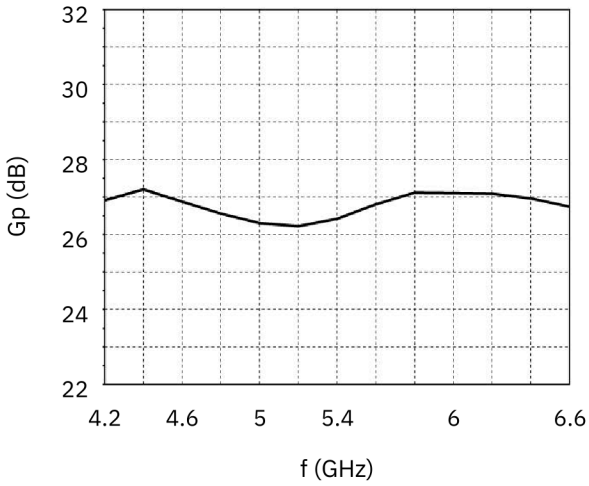
Continuous wave (CW) — Saturated output power; Dynamic drain current; Power-added efficiency; Power gain.

Figure notes: TA=+25°C; Vd=+28V; Vg=-2.8V; Pin=17dBm.









Document notice

Specifications are subject to revision. Before design release, confirm the current document revision and product-specific requirements with LCRF. The approved quotation and order documentation define the supplied configuration.